

Rev. 04/03

Docket No. ELM-2 Cont. 4

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Glenn J. Leedy

Application No.: 10/672,961 Confirmation No.: 9439

Filed : September 26, 2003

For : THREE DIMENSIONAL STRUCTURE

INTEGRATED CIRCUITS (AS AMENDED)

Group Art Unit: 2811

Examiner : Not yet assigned

New York, New York August 11, 2004

Hon. Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

TRANSMITTAL LETTER FOR INFORMATION DISCLOSURE STATEMENT

Sir:

Transmitted herewith is an Information

Disclosure Statement in the above-identified application.

This Statement is submitted:

- [] within three months of the application filing date;
- [X] more than three months from the application filing date but before the mailing date of the first Office Action on the merits.

In accordance with 37 C.F.R. § 1.97, submission of this Statement requires no fee. However, if for any reason a fee is due, the Director is hereby authorized to charge payment of any fees required in connection with this

Information Disclosure Statement to Deposit Account No. 06-1075. A duplicate copy of this letter is transmitted herewith.

Respectfully submitted,

Philip R. foh Registration No. 51,176

Agent for Applicants

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ELM-2 Cont. 4

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P.O. Box 1450

Alexandrian, Virginia 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with 37 C.F.R. §§ 1.56 and 1.97, applicant wishes to call the attention of the Examiner to the following documents:

U.S. Patents

Fujii et al.	Re. 34,893	04/04/95
Foster	2,915,722	12/01/59
Farrand	3,202,948	08/24/65
Lesk	3,559,282	02/02/71
Burkhardt	3,560,364	02/02/71
Emmasingel	3,602,982	09/07/71
Medicus	3,615,901	10/26/71
Napoli et al.	3,716,429	02/13/73
Krishna et al.	3,777,227	12/14/73
Kuipers	3,868,565	02/25/75
Yerman	3,922,705	11/25/75
Wanlass	3,997,381	12/14/76
Stein	4,070,230	01/24/78
Greenwood et al.	4,131,985	01/02/79
Hauser, Jr., et al.	4,142,004	02/27/79

1		00/01/05
Hoeberechts	4,251,909	02/24/81
Kubacki	4,262,631	04/21/81
Shioya et al.	4,394,401	07/19/83
-		•
Trenkler et al.	4,401,986	08/30/83
Thomas et al.	4,416,054	11/22/83
Takagi et al.	4,539,068	09/03/85
Reid et al.	4,585,991	04/29/86
Yasumoto et al.	4,612,083	09/16/86
Belanger et al.	4,617,160	10/14/86
Shimizu et al.	4,618,397	10/21/86
Schmitz	4,618,763	10/21/86
Christensen	4,663,559	05/05/87
Burns et al.	4,684,436	08/04/87
Hatada	4,693,770	09/15/87
Maeda et al.	4,702,336	10/27/87
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Go	4,706,166	11/10/87
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"IC Tower Patent: Simple Technology Receives Patent on the IC Tower, a Stacked Memory Technology," http://www.simpletech.com/whatsnew/memory/@60824.htm (1998).

Alloert, K., et al., "A Comparison Between Silicon Nitride Films Made by PCVD of N_2 -SiH $_4$ /A $_r$ and N_2 -SiH $_4$ /He," Journal of the Electrochemical Society, Vol. 132, No. 7, pp. 1763-1766, (July 1985).

Hendricks, et al., "Polyquinoline Coatings and Films: Improved Organic Dielectrics for IC's and MCM's," Eleventh IEEE/CHMT International Electronics Manufacturing Technology Symposium, "pp. 361-265 (1991).

Knolle, W.R., et al., "Characterization of Oxygen-Doped, Plasma-Deposited Silicon Nitride," Journal of the Electrochemical Society, Vol. 135, No. 5, pp. 1211-1217, (May 1988).

Nguyen, S.V., "Plasma Assisted Chemical Vapor Deposited Thin Films for Microelectronic Applications, J. Vac. Sci. Technol. Vol. B4, No. 5, pp.1159-1167, (Sep/Oct. 1986).

Olmer, et al., "Intermetal Dielectric Deposition by Plasma Enhanced Chemical Vapor Deposition," Fifth IEEE/CHMT International Electronic Manufacturing Technology Symposium - Design-to-Manufacturing Transfer Cycle," pp. 98-99 (1988).

Runyan, W.R., "Deposition of Inorganic Thin Films," Semiconductor Integrated Circuit Processing Technology, p. 142 (1990).

Sze, S.M., "Surface Micromachining," Semiconductor Sensors, pp. 58-63 (1994).

Vossen, John L., "Plasma-Enhanced Chemical Vapor Deposition," Thin Film Processes II, pp. 536-541 (1991).

Wolf, Stanley, "Basic of Thin Films," Silicon Processing for the VLSI Era, pp. 115, 192-193 and 199 (1986).

Copies of the aforementioned documents are listed on the accompanying Form PTO-1449 (submitted in duplicate).

It is respectfully requested that these documents be: (1) fully considered by the Patent and Trademark Office during the examination of this application; and (2) printed on any patent which may issue on this application. Applicant requests that a copy of Form PTO-1449, as considered and initialized by the Examiner, be returned with the next communication.

Consideration of the foregoing in relation to this patent application is respectfully requested.

Respectfully submitted,

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Addressed to:

Commissioner for Patents

P.O. Box 1450

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tyre of Porson Signing

Philip R. Pol

Registration No. 51,176

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FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ELM-2 Cont. 4	APPLICATION NO. 10/672,961
••	NFORMATION DISCLOSURE	APPLICANT Glenn J. Leedy	CONFIRMATION NO. 9439
	STATEMENT BY APPLICANT	FILING DATE September 26, 2003	GROUP 2811

U.S. PATENT DOCUMENTS

EXAMINE R INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
INTIAL	Re. 34,893	04/04/95	Fujii et al.	257	419	7411101111111
	2,915,722	12/01/59	Foster	336	115	
	3,202,948	08/24/65	Farrand	336	115	
	3,559,282	02/02/71	Lesk	438	113	
	3,560,364	02/02/71	Burkhardt	324	207.12	
	3,602,982	09/07/71	Emmasingel	29	577	
	3,615,901	10/26/71	Medicus	148	11.5 R	
	3,716,429	02/13/73	Napoli et al.	156	17	
	3,777,227	12/14/73	Krishna et al.	257	578	
	3,868,565	02/25/75	Kuipers	324	207.26	
	3,922,705	11/25/75	Yerman	357	26	
	3,997,381	12/14/76	Wanlass	156	3	
	4,070,230	01/24/78	Stein	156	657	
	4,131,985	01/02/79	Greenwood et al.	29	580	
	4,142,004	02/27/79	Hauser, Jr. et al.	438	792	-
	4,251,909	02/24/81	Hoeberechts	29	580	
	4,262,631	04/21/81	Kubacki	118	723MP	
	4,394,401	07/19/83	Shioya et al.	427	574	
	4,401,986	08/30/83	Trenkler et al.	340	870.32	
	4,416,054	11/22/83	Thomas et al.	29	572	
	4,539,068	09/03/85	Takagi et al.	156	614	
	4,585,991	04/29/86	Reid et al.	324	158 P	
	4,612,083	09/16/86	Yasumoto et al.	156	633	
	4,617,160	10/14/86	Belanger et al.	264	40.1	
	4,618,397	10/21/86	Shimizu et al.	156	628	
	4,618,763	10/21/86	Schmitz	250	211R	
	4,663,559	05/05/87	Christensen	313	336	
	4,684,436	08/04/87	Burns et al.	216	65	
	4,693,770	09/15/87	Hatada	156	151	

EXAMINER

FORM PTO-1449	ORM PTO-1449 U.S. DEPARTMENT OF COMM PATENT AND TRADEMARK O			'. DOCKET NO 2 Cont. 4	APPLICATION NO. 10/672,961
	FORMATION DISC FATEMENT BY AP			ICANT n J. Leedy	CONFIRMATION NO 9439
	TATEMENT BY A	LIOANT		G DATE ember 26, 2003	GROUP 2811
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4,702,3	336 10/27/	87 Maeda et al.	18	0 197	
4,702,9	936 10/27/		42	7 583	
4,706,	166 11/10/	87 Go	36	1 403	
4,721,9	938 01/26/	88 Stevenson	33	8 4	
4,761,6	81 08/02/	88 Reid	35	7 68	
4,784,7	⁷ 21 11/15/	88 Holmen et al.	15	6 647	
4,810,6	673 03/07/	89 Freeman	43	8 386	
4,825,2	277 04/25/	89 Mattox et al.	25	7 639	
4,857,4	81 08/15/	89 Tam et al.	43	8 619	
4,924,5	589 05/15/	90 Leedy	43	8 6	
4,940,9	016 07/10/	90 Borel et al.	31	3 306	
Re B14	,940,916 11/26/	96 Borel et al.	31	5 306	
4,950,9	08/21/	90 Vranish et al.	32	4 207.23	3
4,952,4			42	8 220	
4,954,8	65 09/04/	90 Rokos	25	7 378	
4,957,8	882 09/18/	90 Shinomiya	43	8 65	
4,965,4	15 10/23/	90 Young et al.	20	0 83 N	
4,966,6	663 10/30/		20	5 656	
4,994,7	35 02/19/	91 Leedy	32	4 158	
5,008,6	04/16/	91 Keogh et al.	32	4 207.17	7
5,010,0	24 04/23/	91 Allen et al.	43	8 659	
5,020,2	19 06/04/	91 Leedy	29	846	
5,034,6	85 07/23/	91 Leedy	32	4 158 F	
5,070,0	26 12/03/	91 Greenwald et al.	43	7 3	
5,071,5	12/10/	91 Findler et al.	15	6 647	
5,098,8	65 03/24/	92 Machado et al.	43	8 788	
5,103,5			29	832	
5,110,3	73 05/05/	92 Mauger	14	8 33.2	
5,111,2	78 05/05/	92 Eichelberger	35	7 75	
5,116,7			43	8 234	
5,130,8	94 07/14/	92 Miller	36	1 393	
5,132,2	44 07/21/	92 Roy	43	8 477	

FORM PTO-1449	ORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			KET NO. . 4	APPLICATION NO. 10/672,961	
	FORMATION DISCLO		APPLICANT Glenn J. Lee		CONFIRMATION NO. 9439	
3	OTATEMENT BY ALL EIGHT			E 26, 2003	GROUP 2811	
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5,151,	775 09/29/92	Hadwin	357	80	Γ	
5,156,		Henager, Jr. et al.	428	334		
5,203,		Zimmerman	445	24		
5,225,		Leedy	324	158		
5,236,		Bower et al.	228	193		
5,262		Bureau et al.	437	183		
5,270,		Bertin et al.	437	209		
5,273,	940 12/28/93	Sanders	437	209		
5,274	270 12/28/93	Tuckerman	257	758		
5,279,	865 01/18/94	Chebi et al.	427	574		
5,284		Nakanishi et al.	437	183		
5,323	035 06/21/94	Leedy	257	48		
5,324,	687 06/28/94	Wojnarowski	437	225		
5,354	695 10/11/94	Leedy	438	411		
5,363	021 11/08/94	MacDonald	315	366		
5,385	909 01/31/95	Nelson et al.	514	291		
5,385	632 01/31/95	Goossen	156	630		
5,420	458 05/30/95	Shimoji	257	622		
5,424	920 06/13/95	Miyake	361	735		
5,426	072 06/20/95	Finnila	437	208		
5,426	363 06/20/95	Akagi et al.	324	239		
5,432	444 07/11/95	Yasohama et al.	324	240		
5,432		Carson et al.	365	63		
5,434		Hauck et al.	324	67		
5,451		Leedy	430	313		
5,453		Leedy	437	203		
5,457		Gurtler et al.	29	895		
5,476		Naruse	437	132		
5,489		Gates	437	208		
5,502		Bertin et al.	365	51		
5,512		Leedy	430	30		
5,527		Pati et al.	430	5		

FORM PTO-1449	-	IT OF COMMERCE ADEMARK OFFICE	ATTY. DOC ELM-2 Cont		APPLICATION NO. 10/672,961	
	FORMATION DISCLO		APPLICANT Glenn J. Leedy		CONFIRMATION NO. 9439	
STATEMENT BY APPLIC		CANT	FILING DAT		GROUP 2811	
	<u></u>					
5,529,	829 06/25/96	Koskenmaki et al.	428	167		
5,534,		Frye et al.	437	209		
5,555,		Toshiaki et al.	365	200		
5,563,		Ramm et al.	437	51		
5,571,		Leedy	437	51		
5,580,		Leedy	430	5		
5,581,		Ludwig et al.	365	63		
5,582,		Pierrat	430	5		
5,583,		Hornbeck	359	291		
5,592,		Leedy	257	347		
5,592,		Leedy	257	619		
5,595,		Heijboer	439	20		
5,606,		Noda	257	226		
5,627,		Tennant et al.	438	113		
5,629,		Leedy	430	313		
5,633,		Leedy	435	228		
5,637,		Val	438	686		
5,654,		Leedy	430	315		
5,654,		Leedy	438	25		
5,656,		Hudak et al.	438	15		
5,675,		Chen et al.	257	774		
5,694,		Ohara et al.	395	566		
5,725,		Leedy	430	315		
5,750,		Weise et al.	427	579		
5,760,		Bozso et al.	257	777		
5,773,		Okonogi	428	446		
5,786,		Rolfson	430	5		
5,793,		Zavracky et al.	257	777		
5,831,		Ray	257	48		
5,834,		Leedy	438	107		
5,840,		Leedy	438	6		
5,856,		Ito et al.	257	370		

FORM PTO-1			MENT OF COMMERCE TRADEMARK OFFICE		ATTY. DOC ELM-2 Con		APPLICATIO 10/672,961	N NO.
	INFORMATION STATEMEN				APPLICAN [*] Glenn J. Le		CONFIRMAT 9439	TION NO.
	STATEMEN	IDIAP	PLICANT		FILING DATE September 26, 200		GROUP 2811	
		·						
	5,868,949	02/09/	99 Sotoka	wa et al.	216	18		
	5,869,354	02/09/			438	110		
	5,870,176	02/09/		et al.	355	53		
	5,880,010	03/09/	99 Davids	on	438	455		
	5,882,532	03/16/	99 Field e	al.	216	2		
	5,902,118	05/11/	99 Hübnei	-	438	106		
	5,915,167	06/22/	99 Leedy		438	108		
	5,946,559	08/31/			438	157		
	5,985,693	11/16/	99 Leedy		438	107		
	5,998,069	12/07/	99 Cutter	et al.	430	5		
	6,008,126	12/28/	99 Leedy		438	667		
	6,020,257	02/01/	00 Leedy		438	626		
	6,045,625	04/04/	00 Housto	n	148	33.3		_
	6,084,284	07/04/	00 Adamid	, Jr.	257	506		
	6,097,096	08/01/	00 Gardne	er et al.	257	777		
	6,133,640	10/17/	00 Leedy		257	778		
	6,194,245 B1	02/27/	01 Tayana	ıka	438	57		
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